

# 3D ACTIVE EDGE SILICON SENSORS - RESULTS and PLANS

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Brunel University UK  
University of Manchester from January 2007



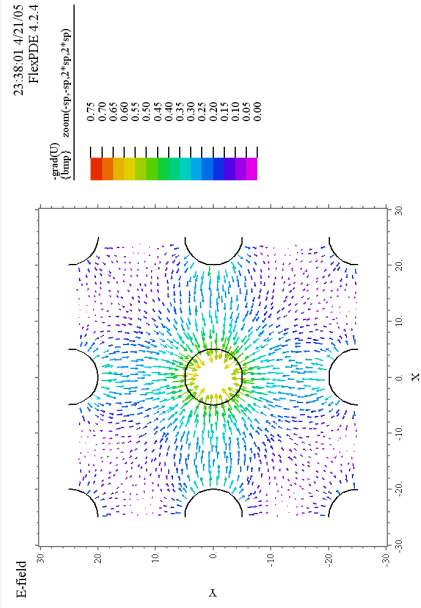
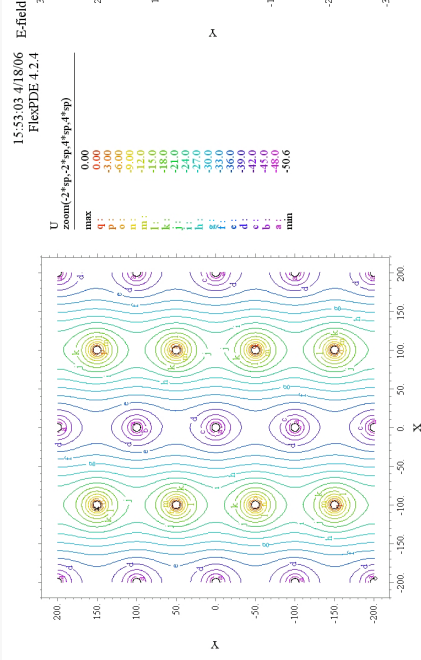
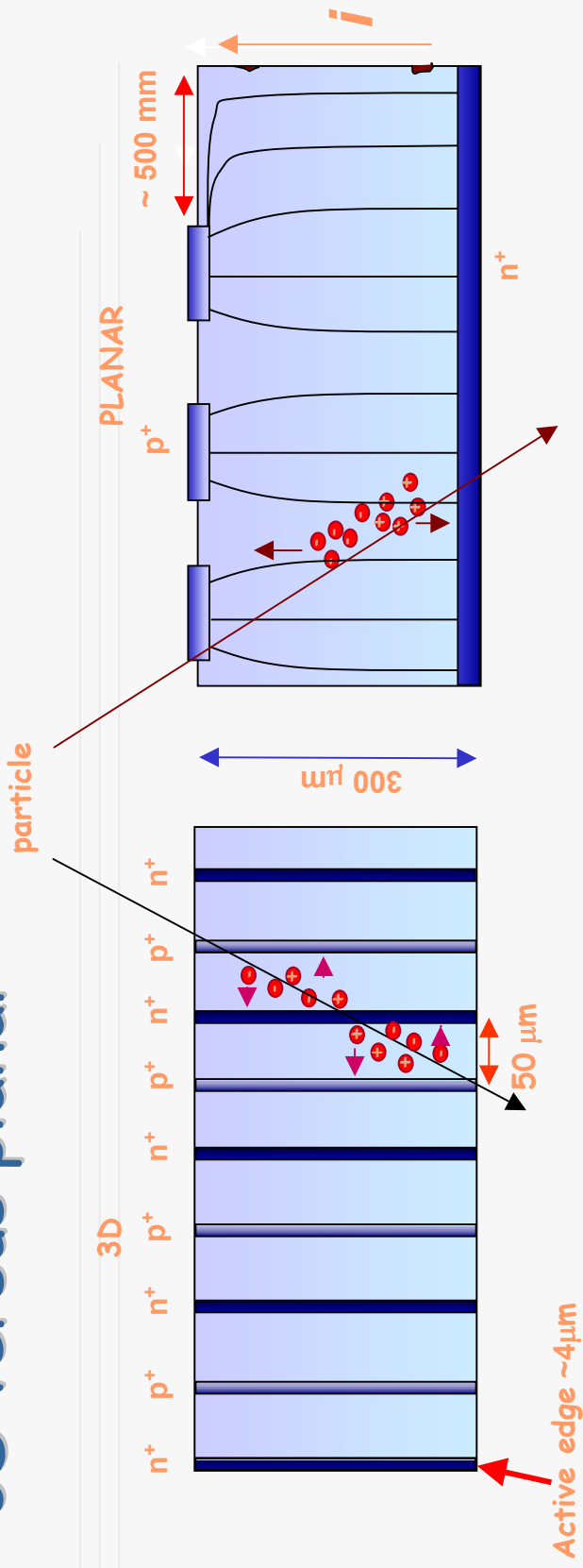
Collaboration

## OUTLINE

- ❖ Modelling
- ❖ Test Beam Results
- ❖ Conclusions and Future plans

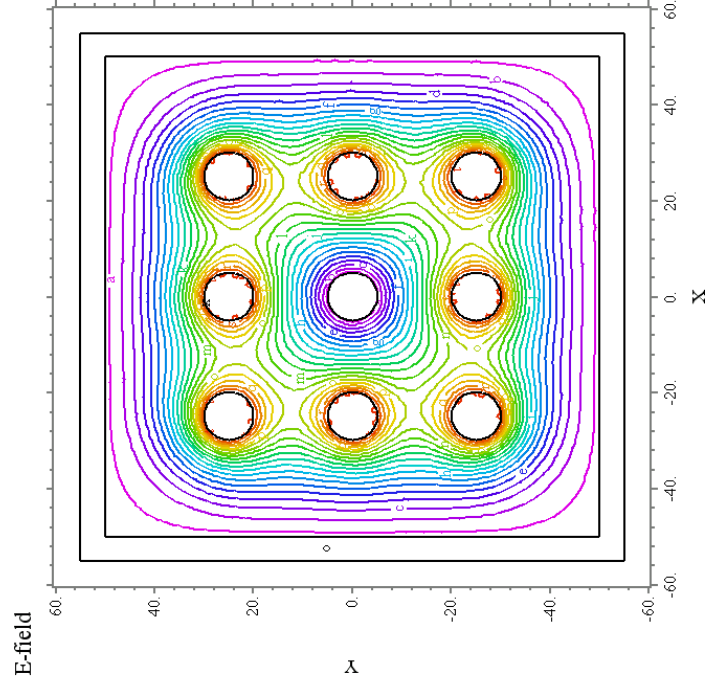
*C. Kenney (MBC), L. Reuen, R. Kohrs, M. Mathes, J. Velthuis, N. Wermes (Bonn Univ.) J. Hasi, A. Kok, (Brunel U.K.) S. Parker (U. of Hawaii) G. Anelli, M. Deile, P. Jarron, J. Kaplon, J. Lozano and the TOTEM Collaboration (CERN), V. Bassetti (Genova), M. Garcia-Scievert, K. Einsweiler (LBL), V. Linhart, T. Slavicheck, T Horadzof, S. Pospisil (Technical University, Praha), M. Ruspa (Torino).*

## 3D versus planar



|                            |                   |
|----------------------------|-------------------|
| 3D                         | planar            |
| $V_{dep} < 5-10 \text{ V}$ | $50-70 \text{ V}$ |
| $Q_{1mp} 24000e^-$         | $24000e^-$        |
| $C 40-80ff$                | $50-200ff$        |

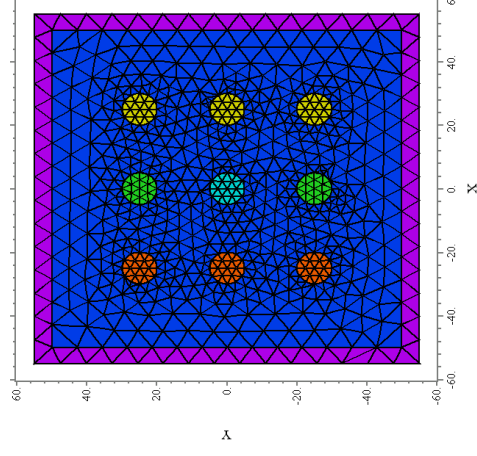
# Device Modelling – e-field, weighting potential, and signals



23:38:01 4/21/05  
FlexPDE 4.2.4

U

|     |       |
|-----|-------|
| max | 0.00  |
| t:  | -0.03 |
| s:  | -0.06 |
| r:  | -0.09 |
| q:  | -0.12 |
| p:  | -0.15 |
| o:  | -0.18 |
| n:  | -0.21 |
| m:  | -0.24 |
| l:  | -0.27 |
| k:  | -0.30 |
| j:  | -0.33 |
| i:  | -0.36 |
| h:  | -0.39 |
| g:  | -0.42 |
| f:  | -0.45 |
| e:  | -0.48 |
| d:  | -0.51 |
| c:  | -0.54 |
| b:  | -0.57 |
| a:  | -0.58 |
| min |       |

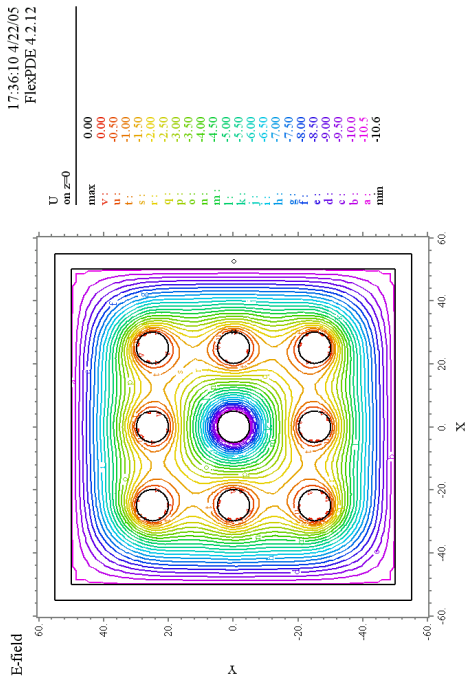


25 micron inter-electrode distance  
p surrounded by n electrodes

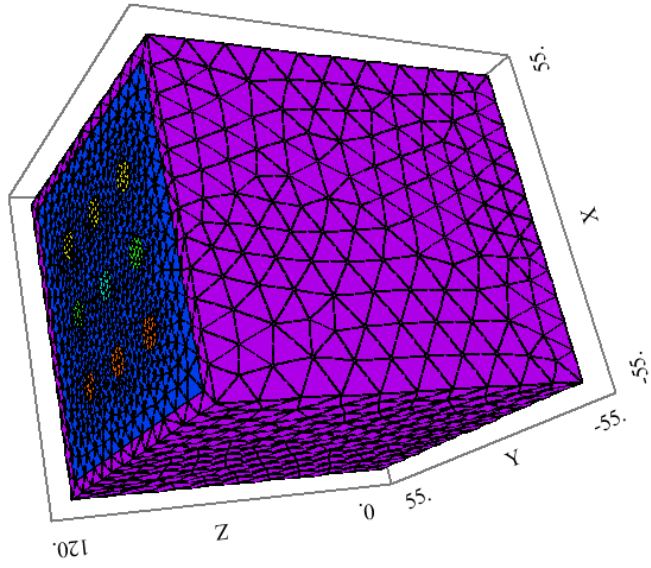
Use general PDE solver (FlexPDE) with modified Poisson equn. to calculate e-field in silicon (depleted/non-depleted).



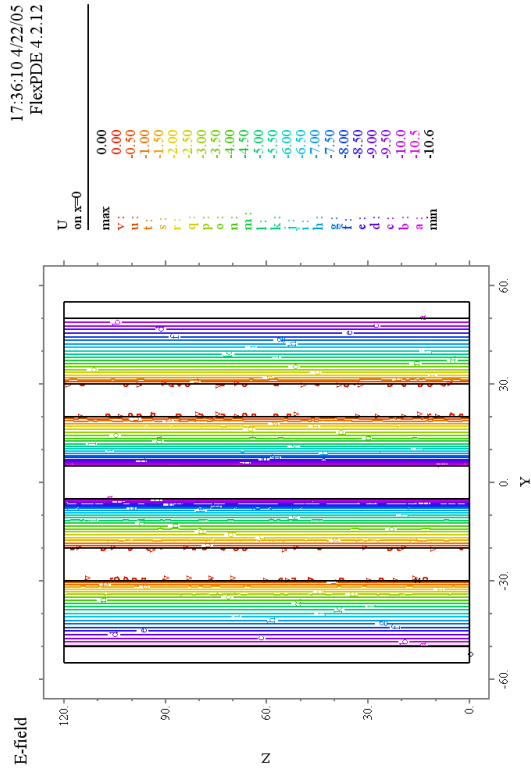
17:36:10 4/22/05  
FlexPDE 4.2.12



ISD: Grid#1 p2 Nodes=164077 Cells=119324 RMS Er= 2.7e-5  
Stage 5 Integral=-73860.38



17:36:10 4/22/05  
FlexPDE 4.2.12

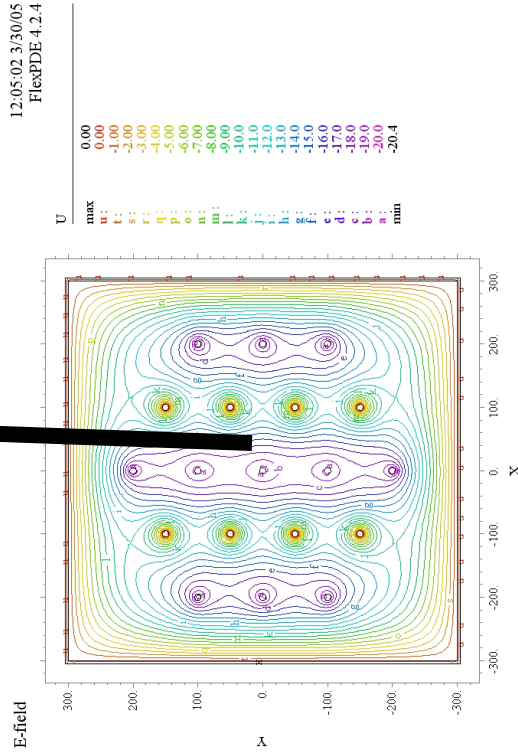
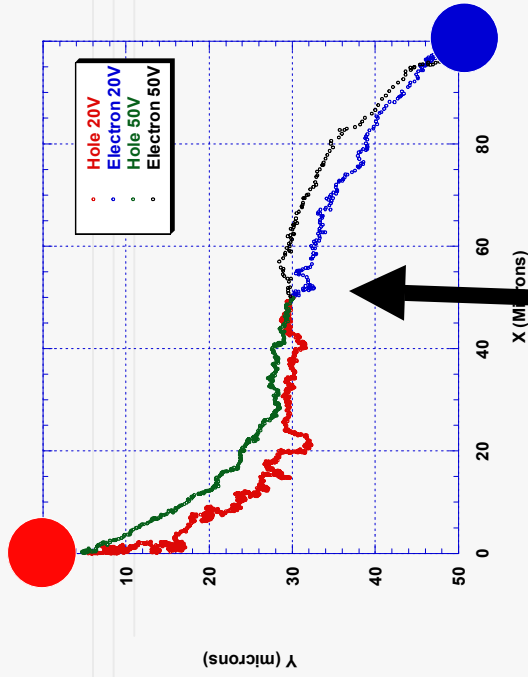


ISD: Grid#1 p2 Nodes=164077 Cells=119324 RMS Er= 2.7e-5  
Stage 5 Integral=-70370.77

**Can solve in 3D if necessary**

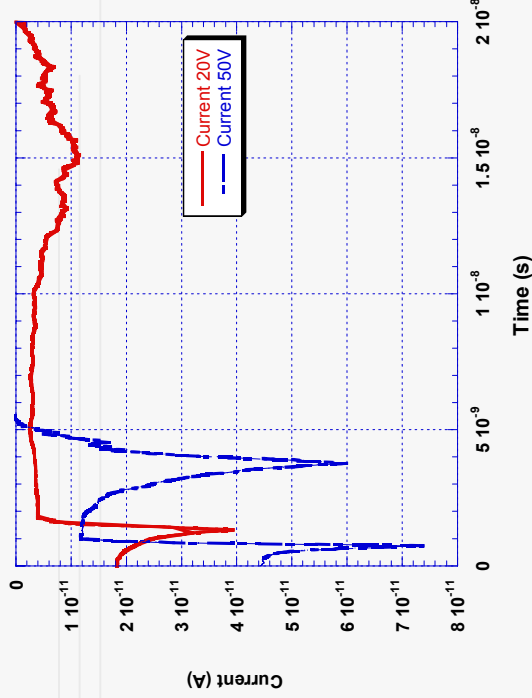
**Stanford 3D detector has same field whatever the depth.**

# e/h paths in device - includes diffusion



I3DqInov: Grid#1 p2 Nodes=14573 Cells=7164 RMS Err= 1.1e-4  
Stage 10 Integral=-.3805349.

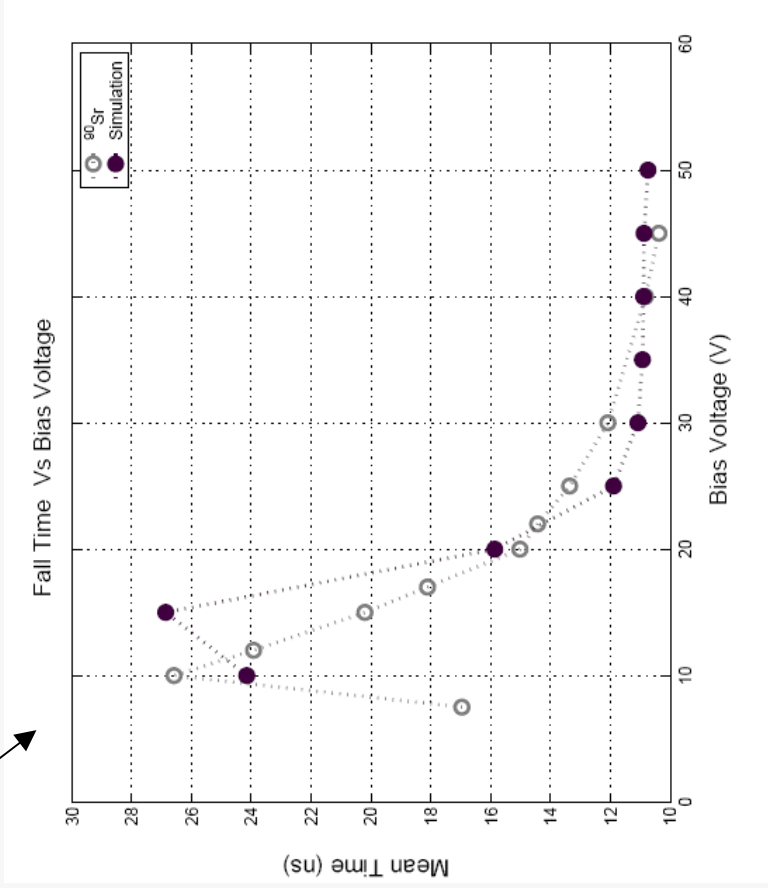
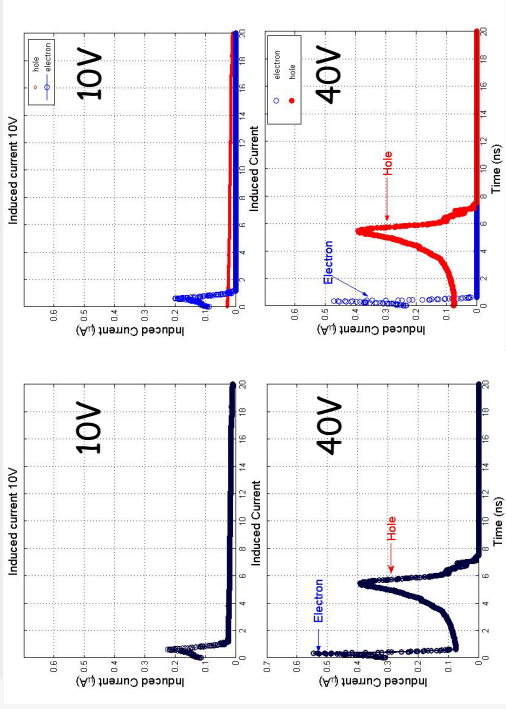
# Current signal at p+ 3Dc



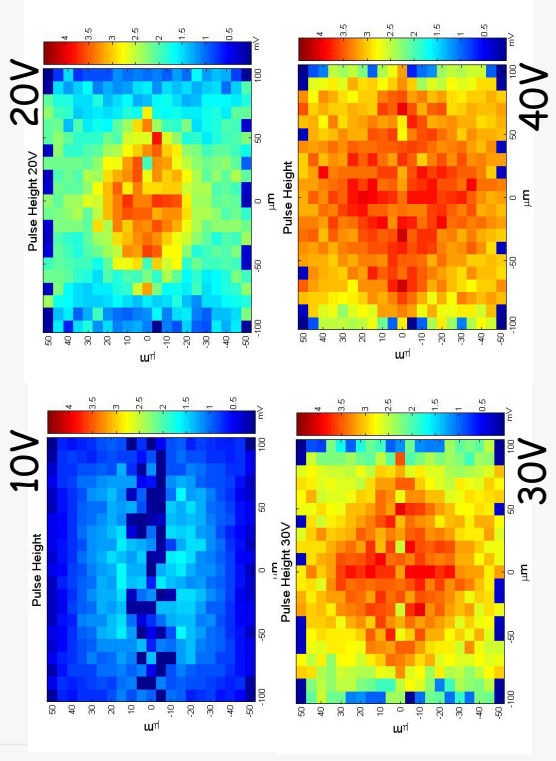
**100 micron inter-electrode strip connection**  
**Mainly affects fall time**

# 3D modelling and data fit

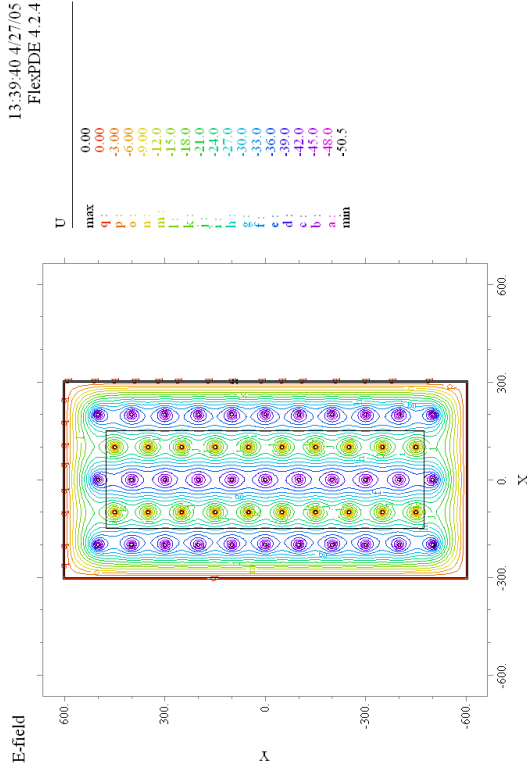
100 micron p/n electrode spacing. 3D Strip



Simulation of signals fall time distribution over a cell (full dot) and <sup>90</sup>Sr data (open dot)



# Capacitance Calculation



Equipotentials – 50V

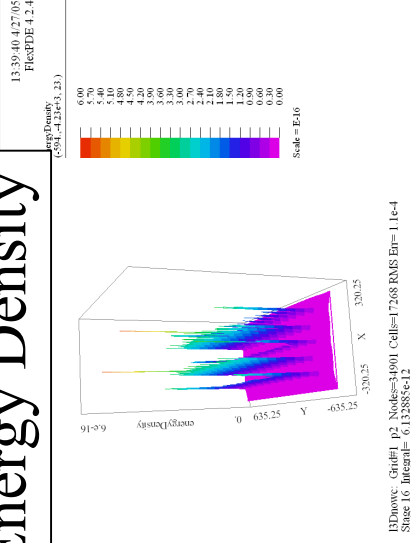
$$\text{Energy Density} = (1/2) * \underline{E} \cdot \underline{D} = (1/2) * \epsilon \underline{E} \cdot \underline{E}$$

Integrate this over the volume...

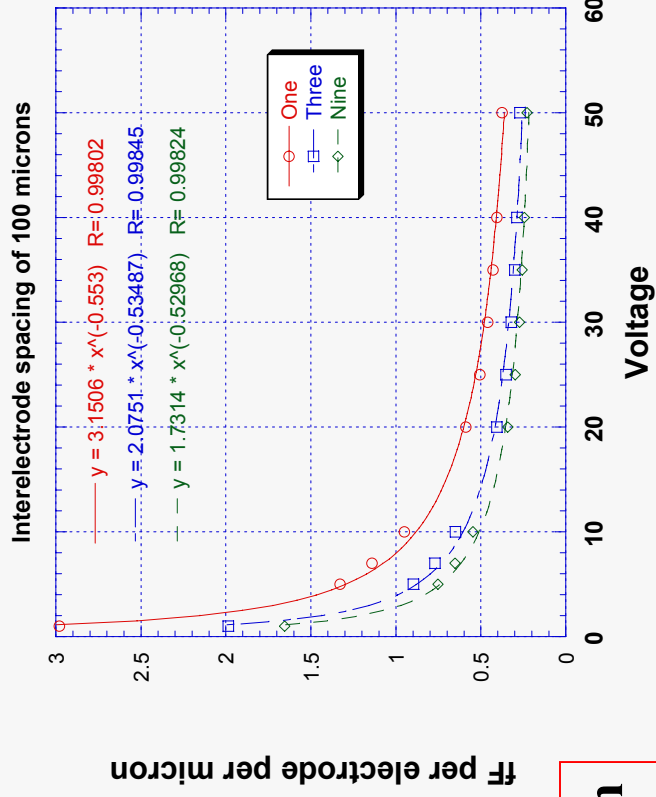
$$C = 2 * (\text{Total Energy Density}) / V^2$$

**Full depletion – 0.25 fF/electrode/micron  
125 micron gives 31 fF**

# Energy Density

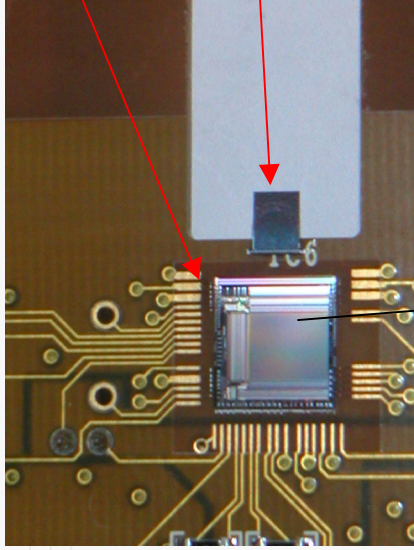


# Results for 1, 3 and 9 electrodes



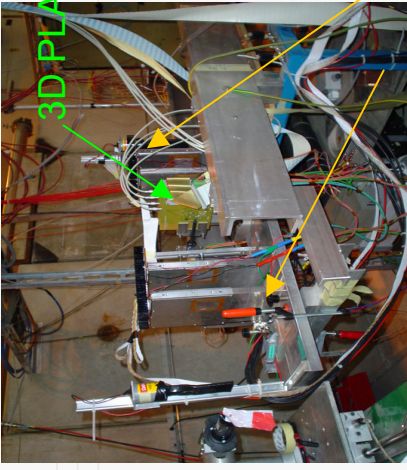
Ratio one to nine ~ 0.6

## Efficiency (TOTEM X5-beam area) - 2003



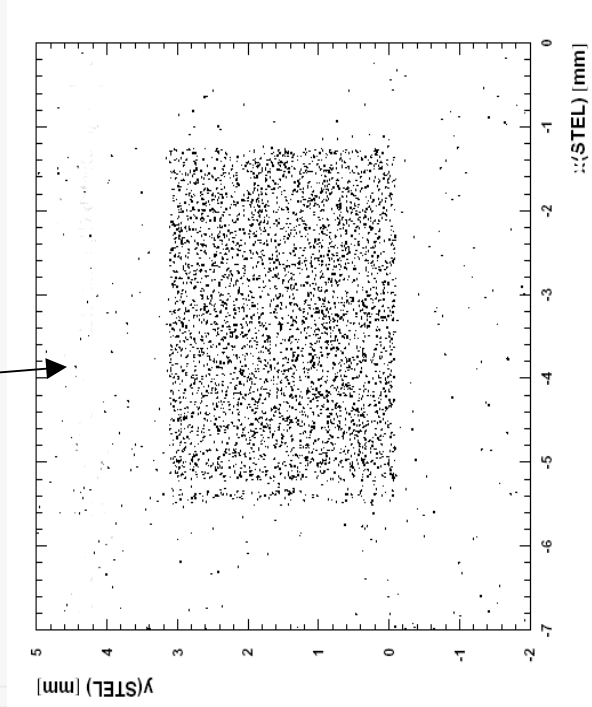
SCTA READOUT CHIP\*

3.195 x 3.9 mm<sup>2</sup>  
3D SENSOR  
Thickness=180 μm  
n-type Si 4kΩ-cm



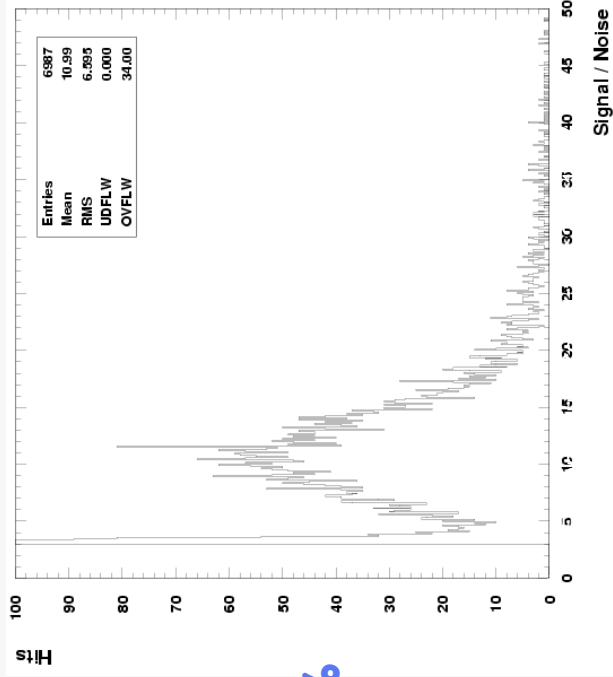
3D PLANES

REFERENCE  
TELESCOPE



S:N=14:1

Efficiency= 98%

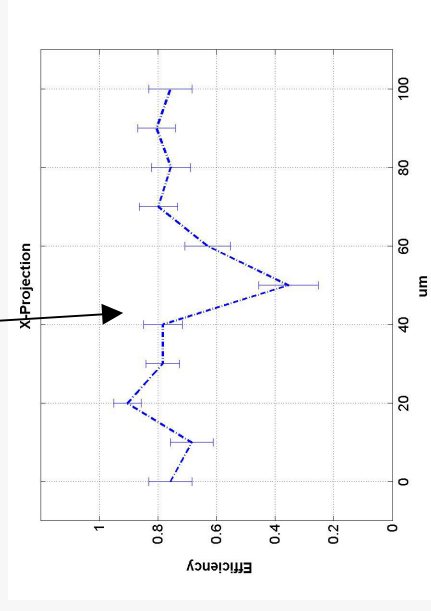
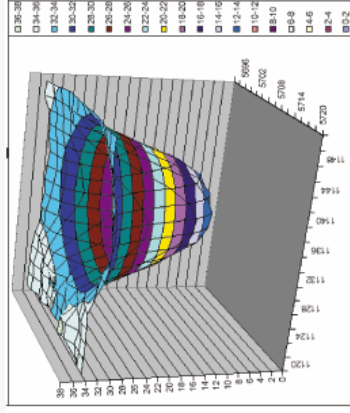
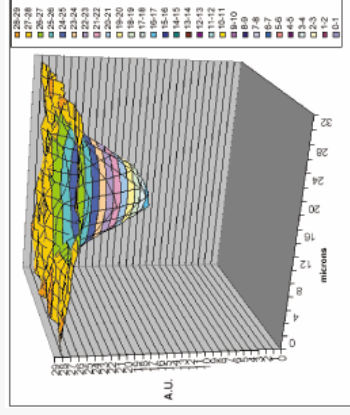
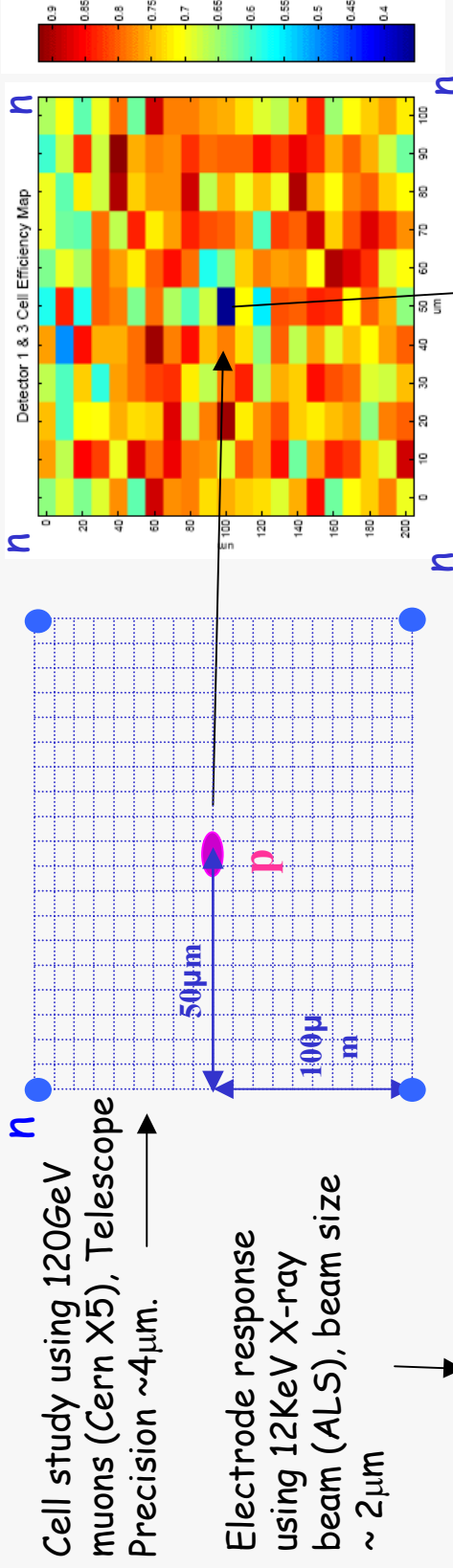




# Efficiency: p and n electrodes response

Electrodes area  $\sim 1.8\%$  of total area

A. Kok PhD thesis



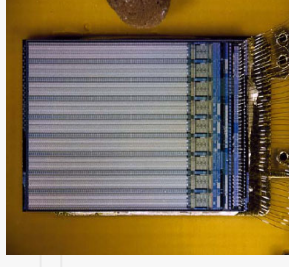
40% reduction in count efficiency at p-electrode

Differences between N and P:  
Grain size of poly, Diameter, Diffusion rate, Trapping, Doping

# Yield + Large area : FP420/Atlas pixel

3Dc

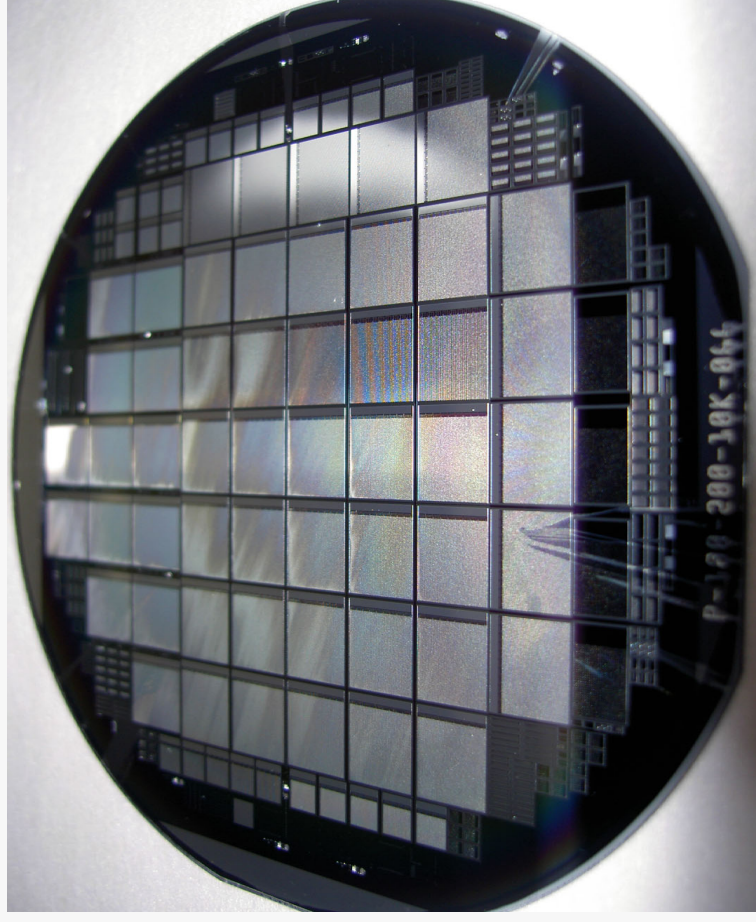
Atlas chip picture from Bekerle Vertex03



| DIMENSIONS                                     | RO SIGNAL                      | Technology                     | BUFFER/speed                    |
|--|--------------------------------|--------------------------------|---------------------------------|
| 50x400 $\mu\text{m}^2$<br>7.2x8mm <sup>2</sup> | binary and time over threshold | 0.25 $\mu\text{m}$ IBM CMOS6SF | 2 - 6.4 $\mu\text{s}$<br>40 MHz |

- 32 3E ATLAS Single Chips
- 6 4E ATLAS Single Chips
- 6 2E ATLAS Single Chips
- Quarter Size ATLAS Chips
- ATLAS Test Structures
- Other structures

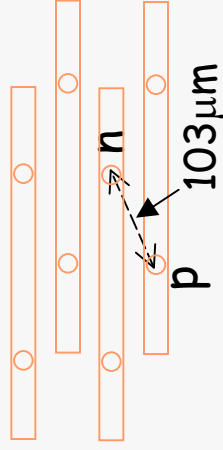
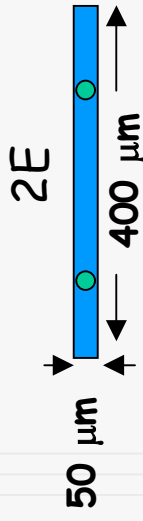
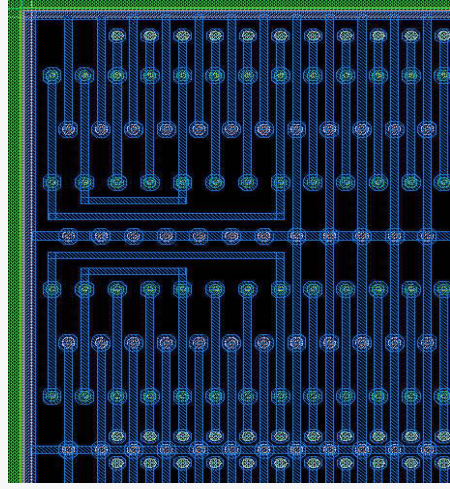
Thickness <250  $\mu\text{m}$ >  
p-type substrate 12k $\Omega\text{cm}$



**10 wafers completed : Yield on one wafer ~80%**

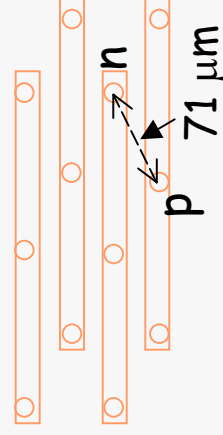
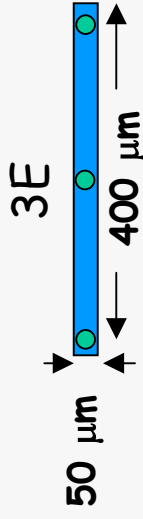
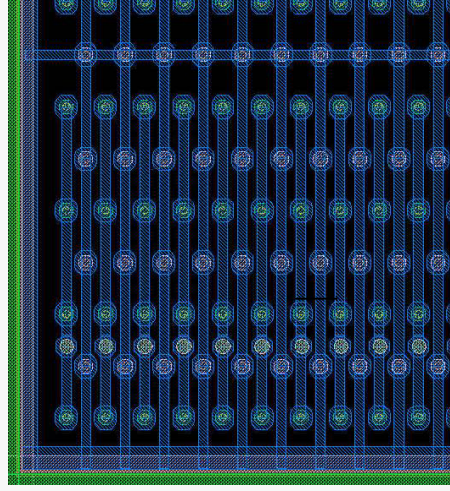
# 3D FP420/Atlaspix electrode configurations

El. 4%



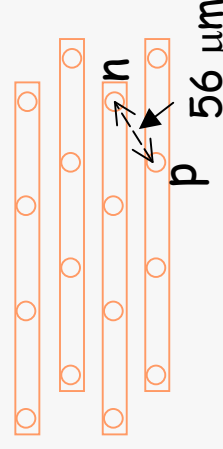
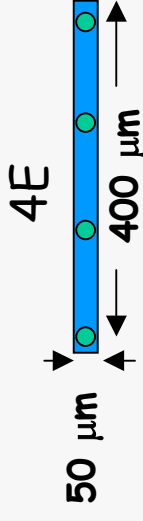
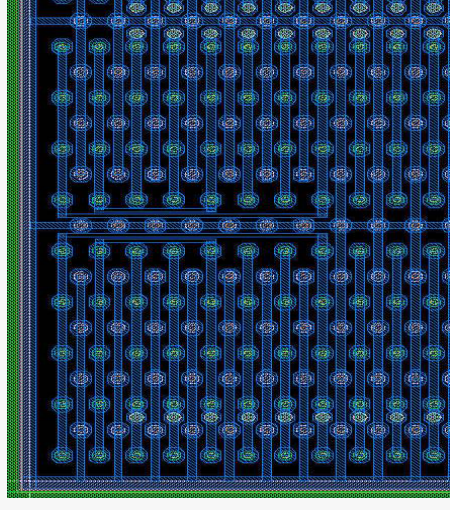
$V_{fd} \sim 20\text{V}$

El. 6%



$V_{fd} \sim 8\text{V}$

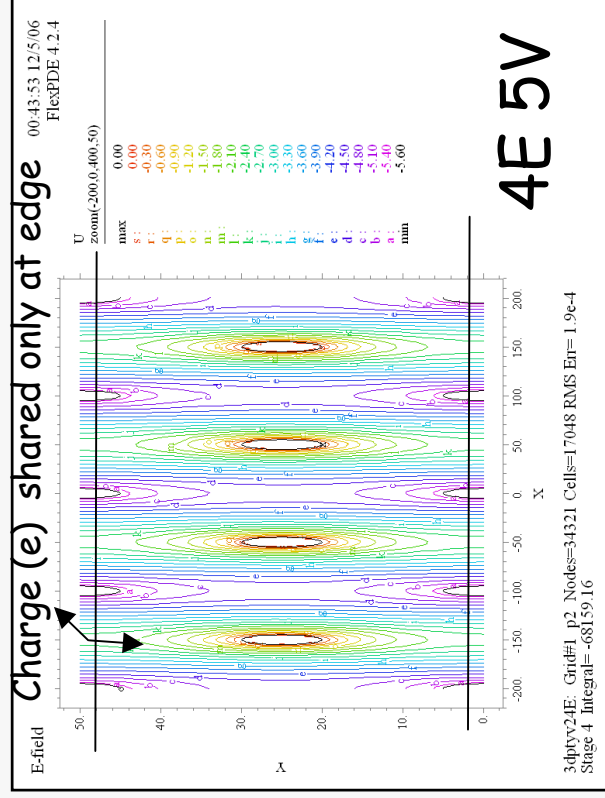
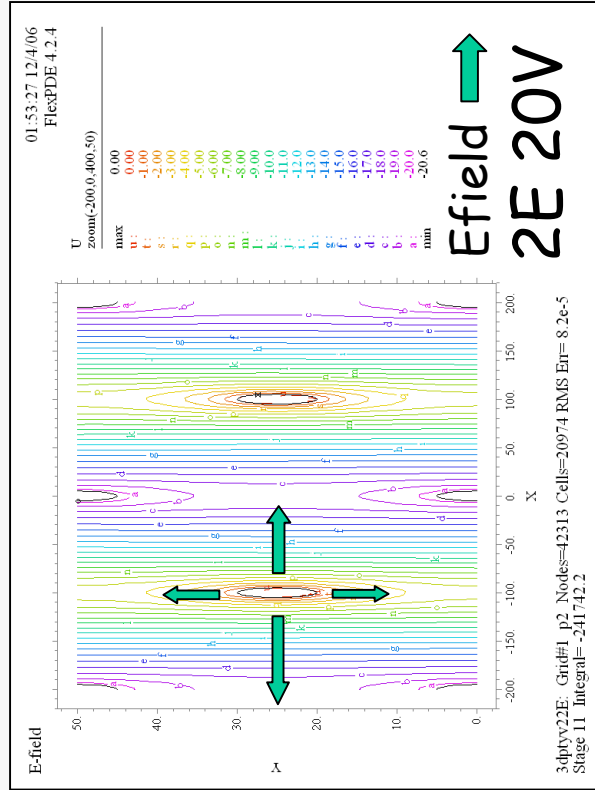
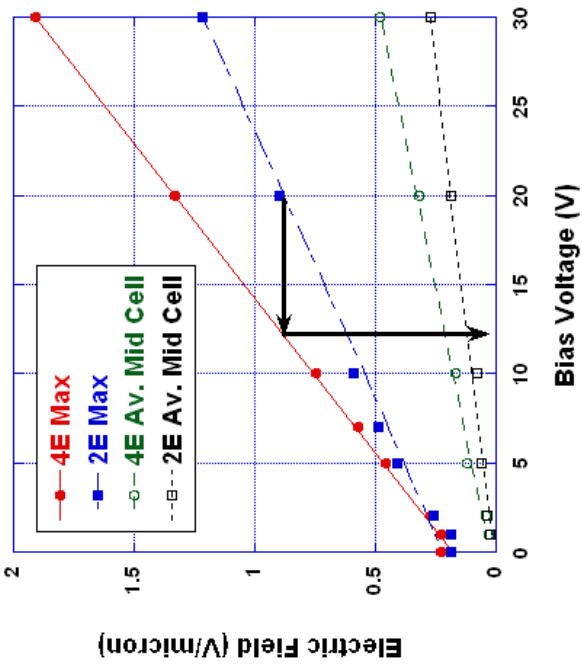
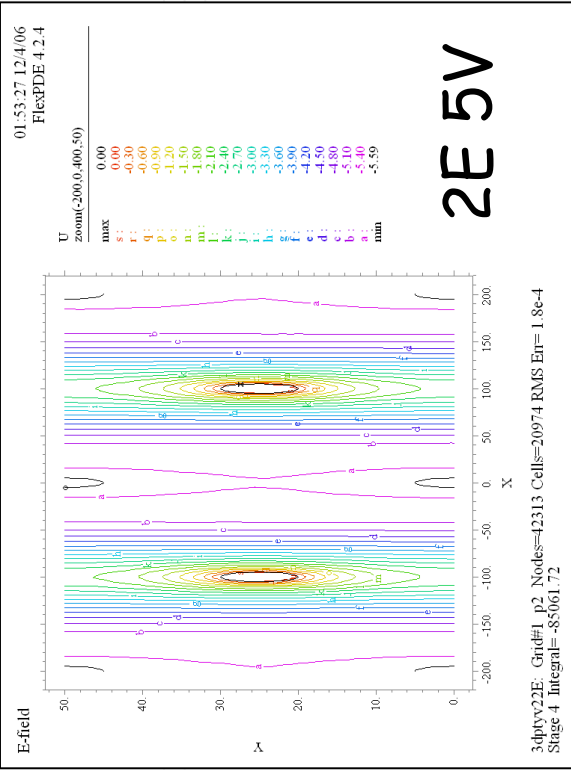
El. 8%



$V_{fd} \sim 5\text{V}$

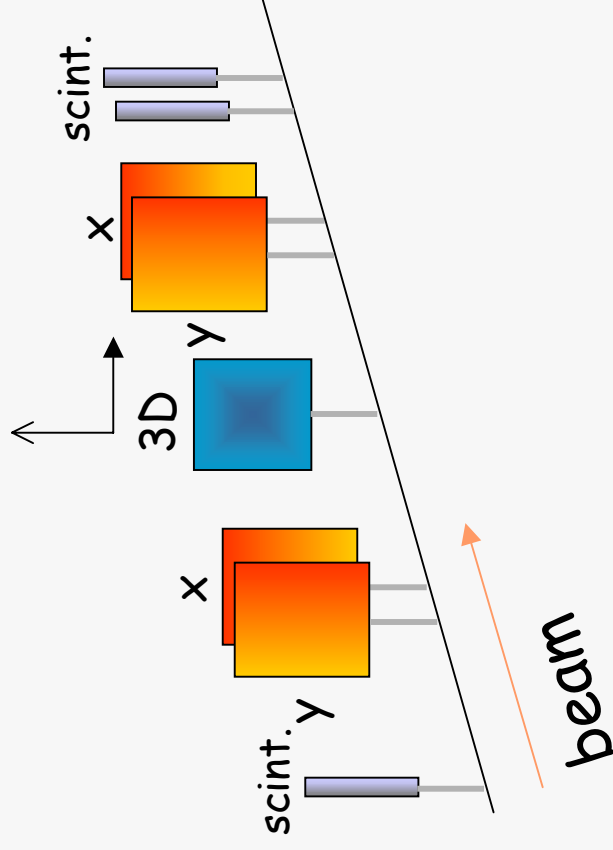
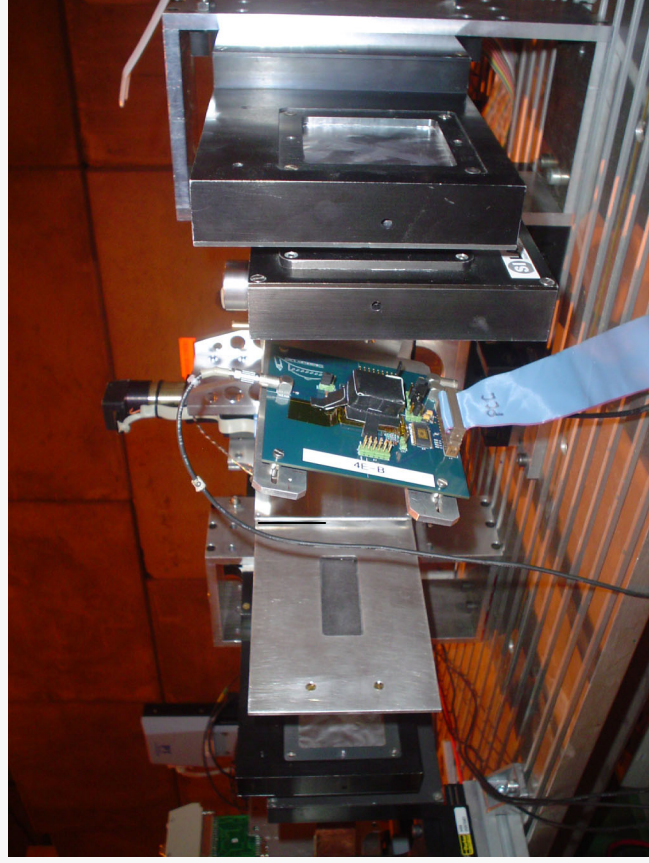
# Equipotentials in 2E and 4E detectors

3DC



# Aug. 17 Sept. 3, 2006 H8 Cern beam line

# 3Dc



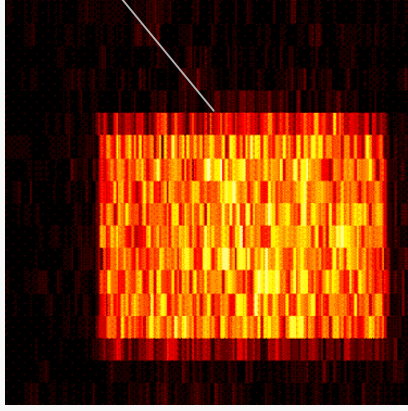
Telescope, daq and on-line monitor by Lars Reuen, Atlas pixel setup and data conversion Markus Mathes (Bonn group)

100 GeV  $\pi^-$   
Triggers: 3x3 mm<sup>2</sup>, 12x12 mm<sup>2</sup>

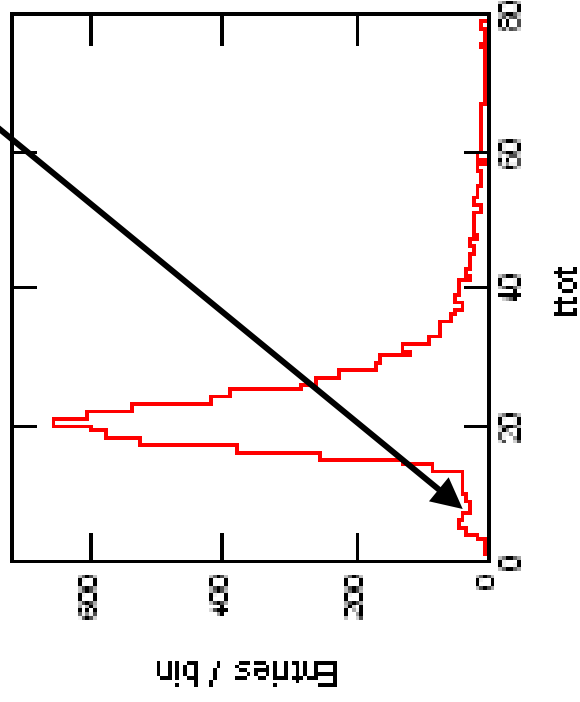
$V_{bias} = 30V$  Threshold =  $4000e^-$

# 3D-2E-A preliminary

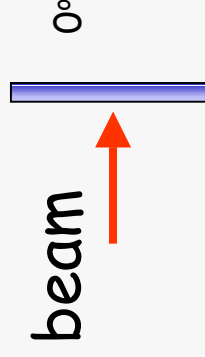
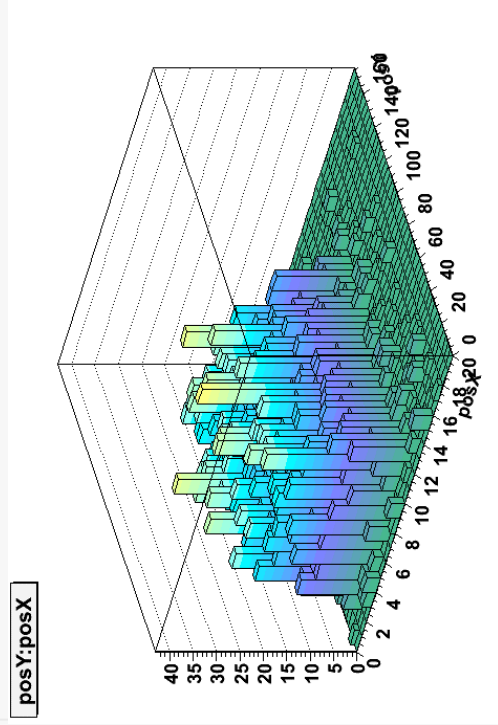
Track through electrode ?



run1066



hitmap with the 12x12 mm² trigger



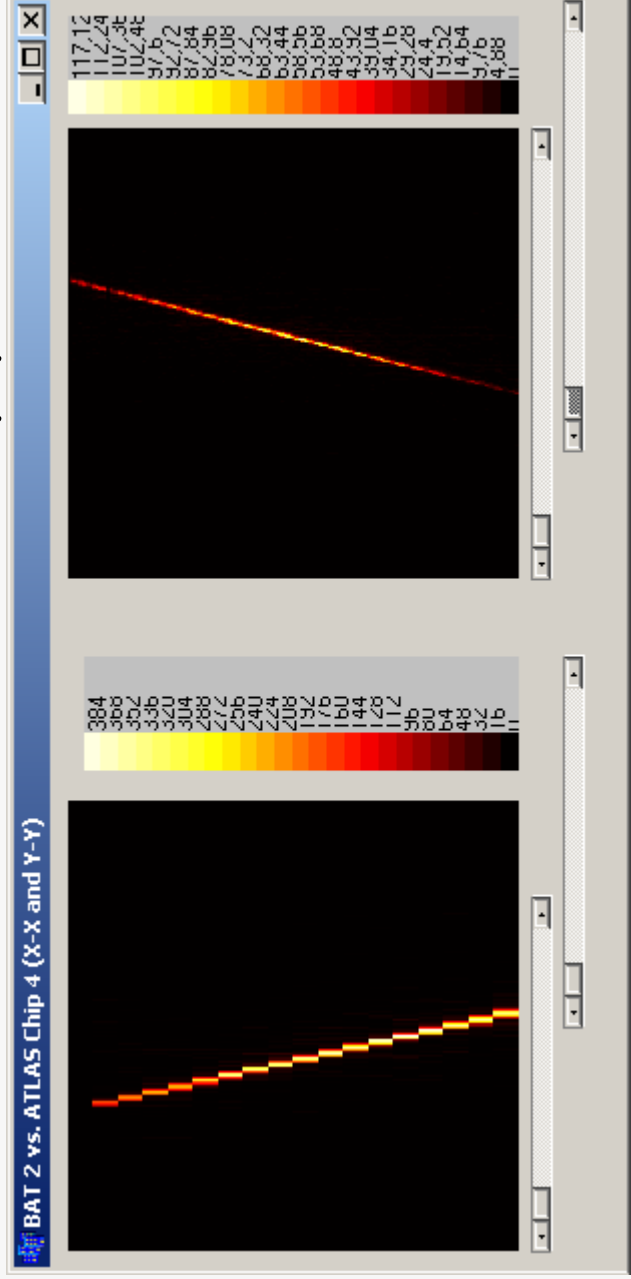
hitmap with the 3x3 mm² trigger

# 3DC

## 3E-G correlation plots and hit maps

X-X

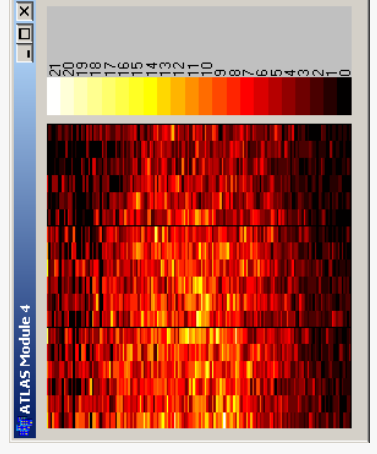
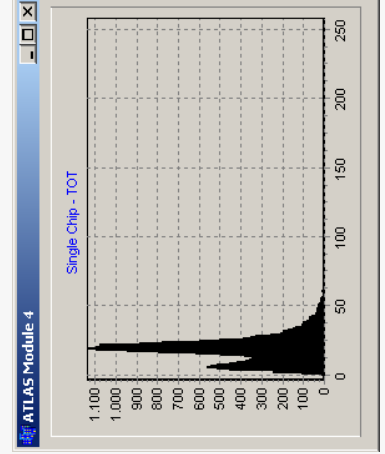
Y-Y



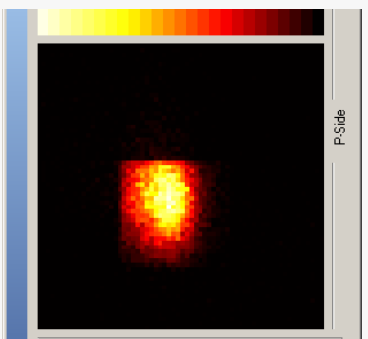
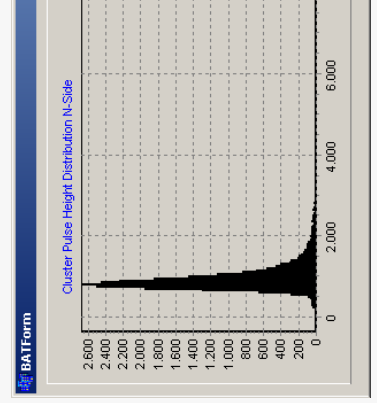
$V_{\text{bias}} = 15V$

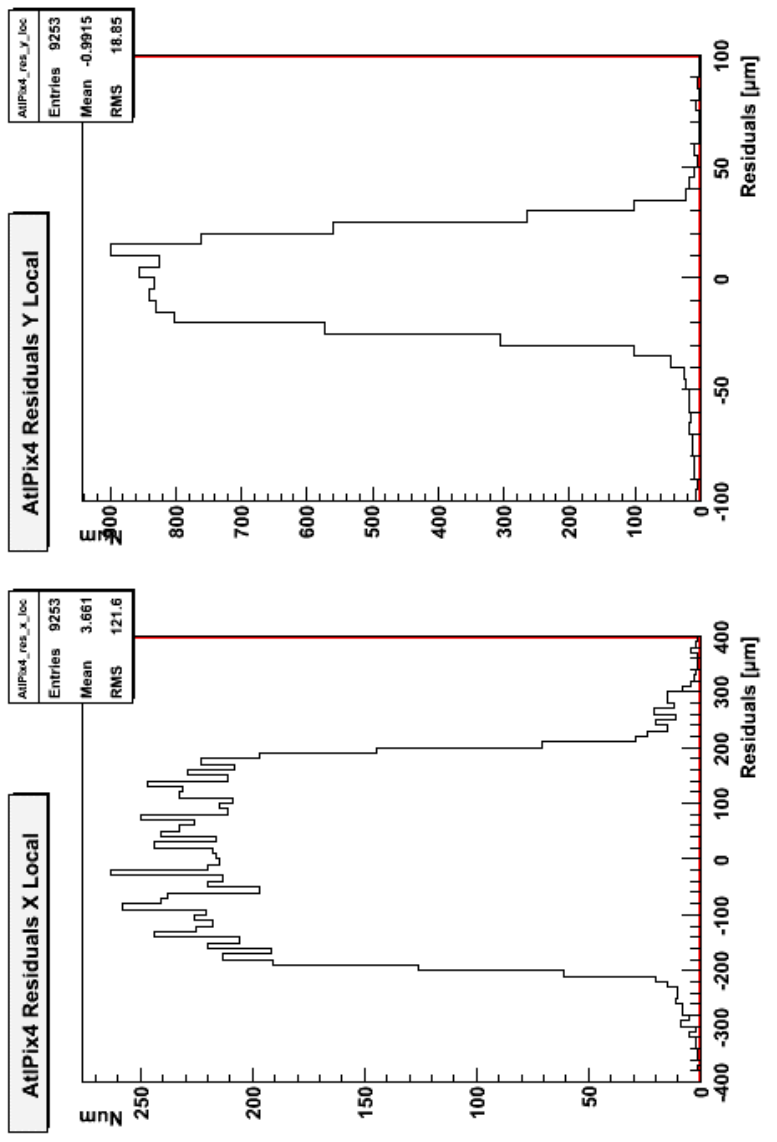
$Th. = 4000e^-$

## Tot 3D



## Telescope





*Thanks to M. Mathes, Bonn*

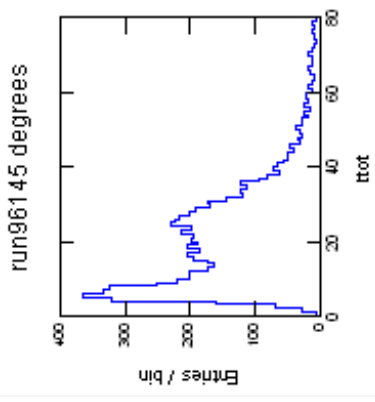
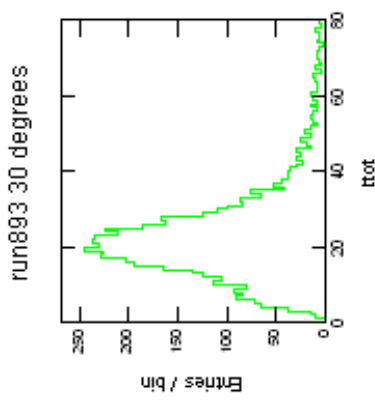
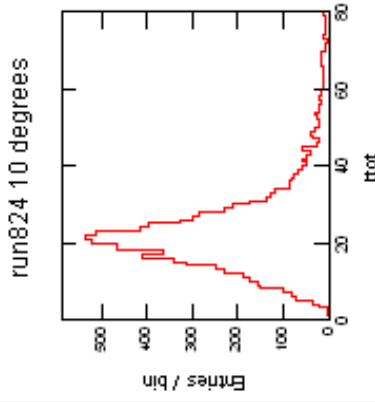
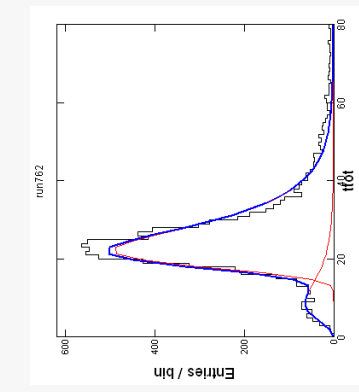
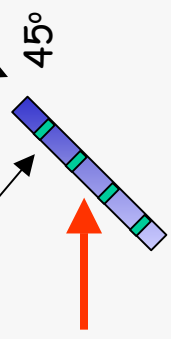
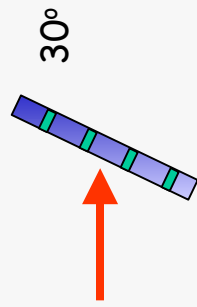
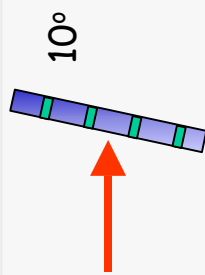
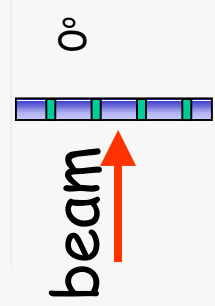
**Tracking to check resolution, efficiency started.  
Much to do.**



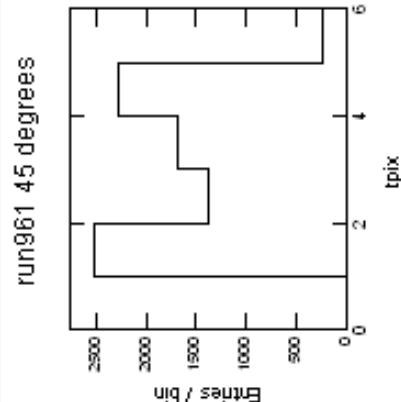
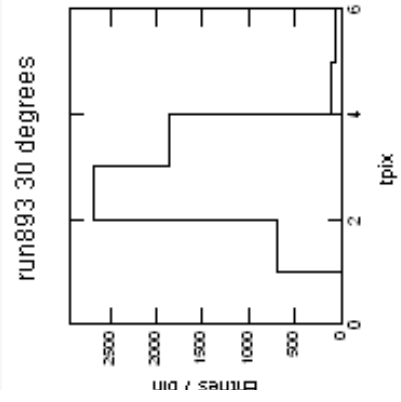
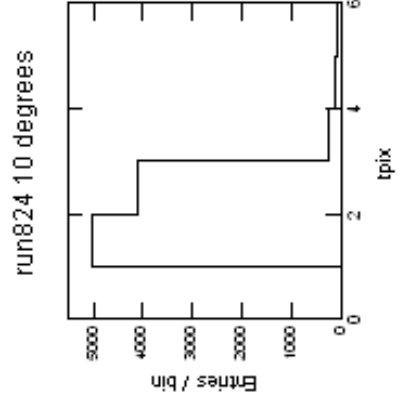
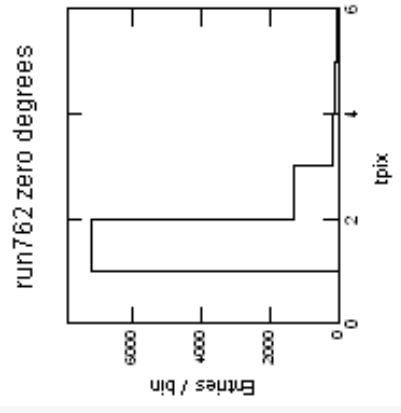
# 4E electrode angular response - preliminary 3Dc

$V_{\text{bias}} = 20\text{V}$  Th. =  $4000e^-$

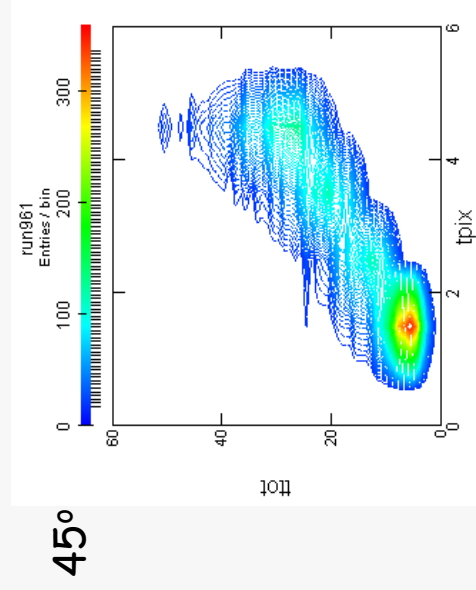
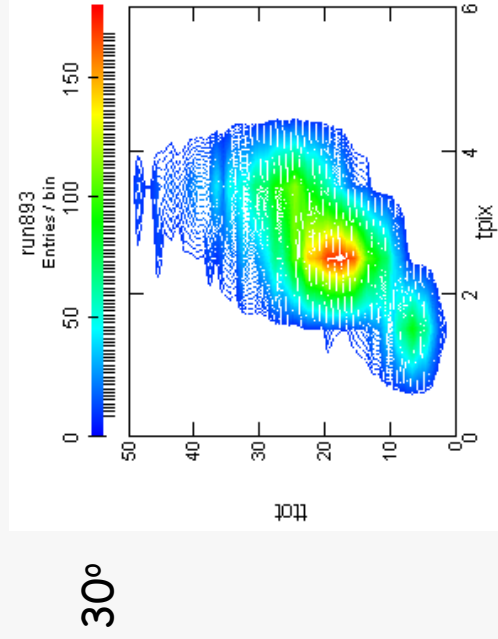
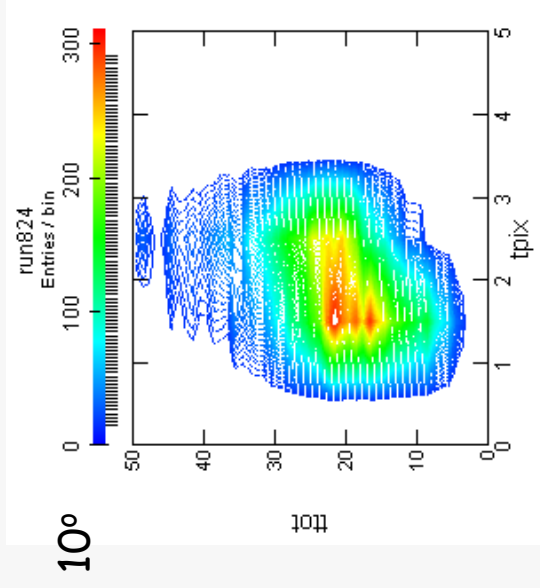
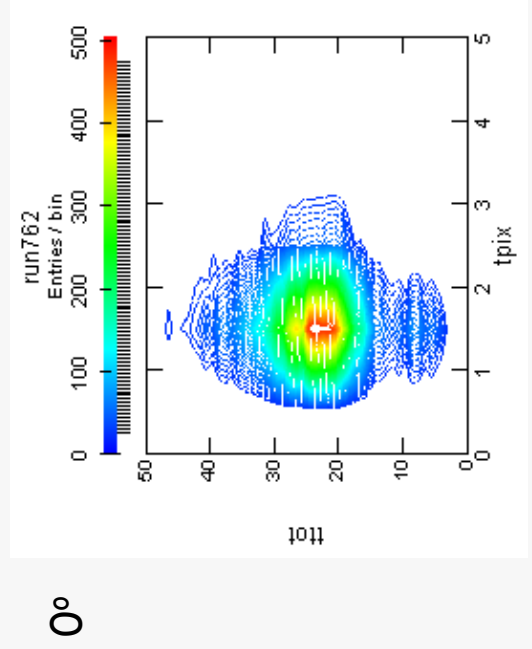
1 pixel cross section  $50 \times 250$



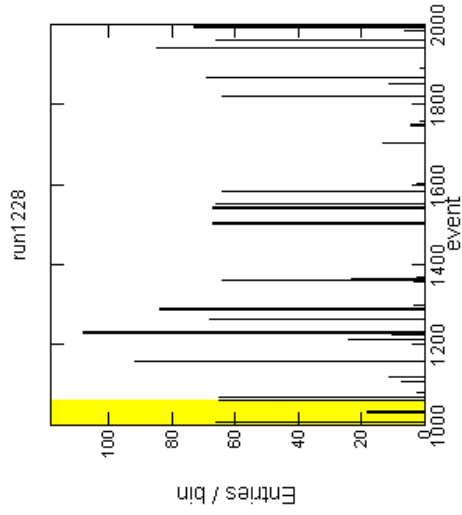
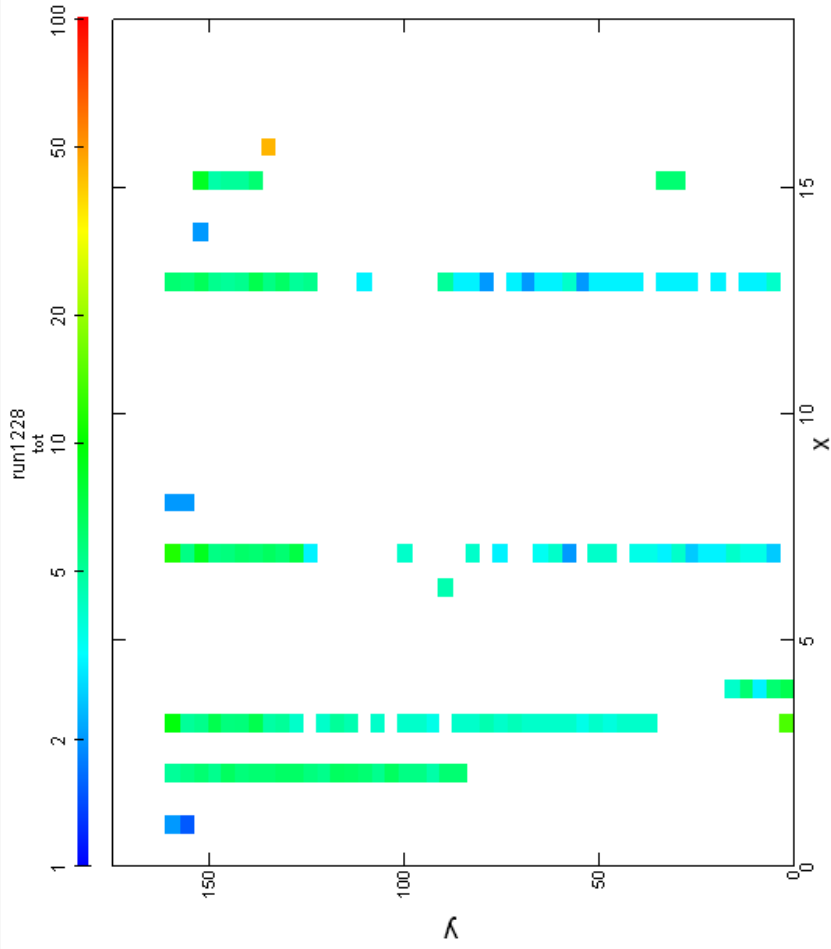
~82 % one pixel



# 4E- Signal size versus cluster size



# 90 Degree data – run 1228

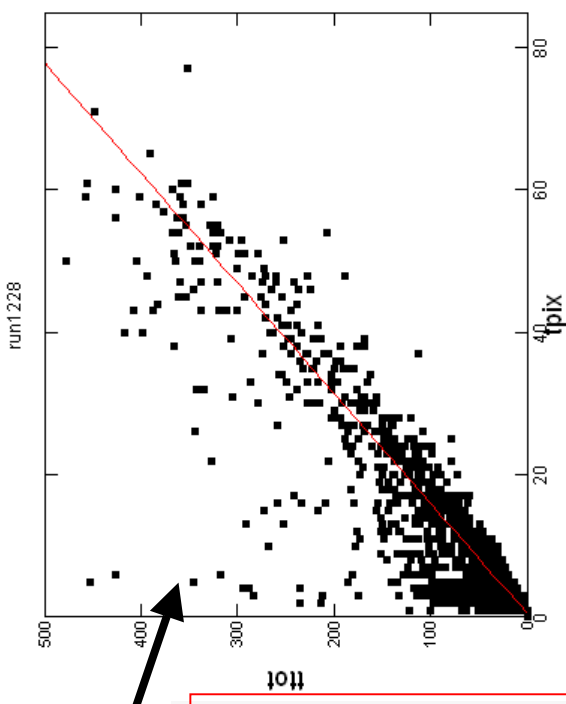
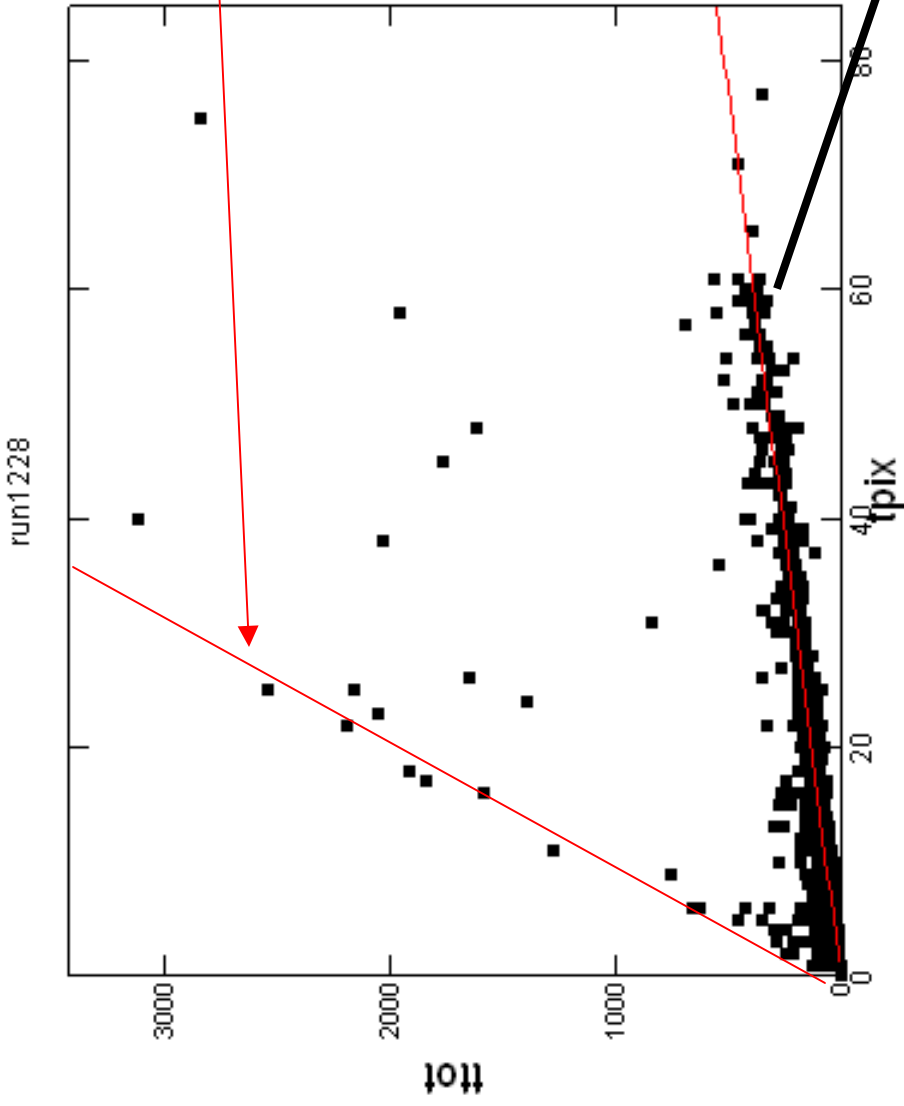


Several events on one plot

Nuclear Recoils???

V. Preliminary

90 degree data



For MIP's  
~6 counts/pixel  
Or 6 counts per 50 micron  
Zero degree get 24 ADC counts  
i.e. wafer thickness =  $4 * 50 = 200$  micron

# Conclusions and future plans

The results so far:

- ❖ Speed of response - data and modelling
- ❖ Edge response, Data from tests as XLS, CERN
- ❖ Efficiency, Data from tests at CERN
- ❖ Rad. Hardness - data and modelling in progress.
- ❖ 3D strip, 3D/planar, 3D pixel detectors made and tested.

For 3D sensors fabricated at Stanford

Will need to further study the test beam data and backup with detector modelling

{ charge sharing - not like a planar silicon detector, check the efficiency versus cell position  
check the electrode response,  
check the spatial resolution - can one do better with cluster size  $> 1$  ? }

We have millions of tracks for 2E, 3E, 4E detectors at several angles.

WORK driven by application in TOTEM, FP420 and ATLAS pixel upgrade.

Team has driven the R&D work to make these applications possible using PPARC funding.

Team: Cinzia DaVia (Tech. Coordinator, FP420), Angela Kok (now at SINTEF)

Jasmine Hasi (based at Stanford), Steve Watts

Now backed up by engineering support at Manchester - Scott Kolya, Ray Thompson.

Collaboration: Stanford/MBC, Hawaii, LBL, Prague, Bonn, CERN.

2006 - Collaboration with SINTEF, Univ. Oslo formed.

Keen to drive forward the ATLAS upgrade work and obtain further PPARC funding.